

Post-Deposition Treatment Boosts CIGS Solar Cell Performance

Highlights in
Research & Development

NREL's use of potassium fluoride process improves the open-circuit voltage and conversion efficiency.

Cu(In,Ga)Se₂ (CIGS) solar cells that are fabricated using two-step selenization processes often exhibit low open-circuit voltage (V_{oc}). National Renewable Energy Laboratory (NREL) scientists have found a way to improve V_{oc} without using a more complex three-stage co-evaporation process.

Previously, NREL investigated the two-step selenization process using two different evaporated precursors—stacked metal precursors and Se-containing precursors. These experiments led to a 16.2%-efficient solar cell fabricated from the Cu/Ga/In stacked metal precursor. But the goal was to increase the efficiency and decrease the time needed for selenization. To accomplish efficiency gains, the V_{oc} needed to be increased.

The two-step selenization process has a few limitations. First, Ga segregation toward the back of CIGS films degrades performance due to lower V_{oc} . This can be alleviated by adding a sulfurization step to widen the bandgap near the CIGS surface. Second, these films lack a precisely engineered surface. A desired Cu-depleted surface region can be created using a three-stage co-evaporation process. The challenge with the two-step selenization process is to produce a similar surface without adding a third stage of Ga and In.

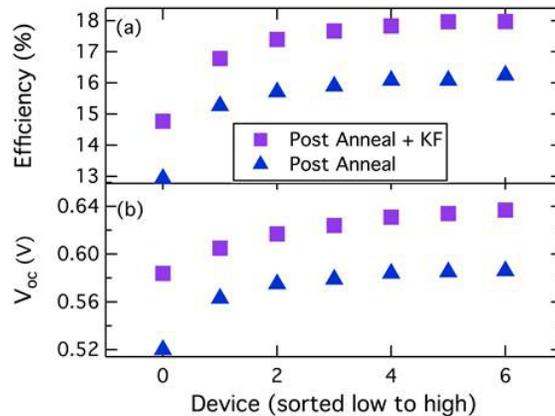
NREL found that the V_{oc} of solar cells made from a Cu/Ga/In stacked metal precursor can be increased by using a potassium fluoride (KF) post-deposition treatment. A two-step selenization process that included this post-deposition treatment led to an 18.6%-efficient CIGS device with a favorable V_{oc} of 0.709 volt.

In addition, efficiency and fill factor values were also improved. For devices made from the same CIGS absorbers, the KF treatment improved efficiencies by 1.5%–1.9%, which resulted from V_{oc} values being boosted by 48–70 millivolts. In one case, fill factor was improved by 2.9%.

The KF post-deposition treatment even improved the V_{oc} and efficiency of previously grown CIGS solar cells that were treated at a later time.

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Reference: Mansfield, L.M.; Noufi, R.; Muzzillo, C.P.; Dehart, C.; Powers, K.; To, B.; Pankow, J.W.; Reedy, R.C.; Ramanathan, K. (2014). "Enhanced Performance in Cu(In,Ga)Se₂ Solar Cells Fabricated by the Two-Step Selenization Process with a Potassium Fluoride Post-Deposition Treatment." *IEEE J. Photovoltaics*, forthcoming.



These two plots show the (a) efficiency and (b) open-circuit voltage of devices made from films with a KF post-deposition treatment (purple squares) and without (blue triangles).

Key Research Results

Achievement

NREL applied a KF post-deposition treatment to solar cells made from a Cu/Ga/In stacked metal precursor.

Key Result

A two-step selenization process that included this KF post-deposition treatment led to an 18.6%-efficient CIGS device with a favorable V_{oc} of 0.709 V.

Potential Impact

NREL's approach precludes the need to use a more complex three-stage co-evaporation process to improve CIGS solar cell performance.

NREL is a national laboratory of the U.S. Department of Energy, Office of Energy Efficiency and Renewable Energy, operated by the Alliance for Sustainable Energy, LLC.

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